



# 2SC5298

## Ultrahigh-Definition CRT Display Horizontal Deflection Output Applications

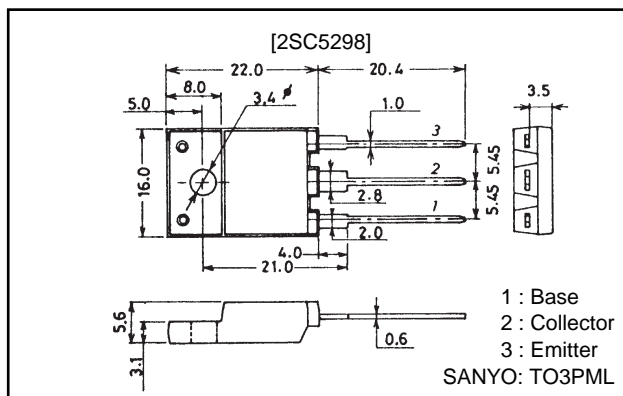
### Features

- High Speed :  $t_f=100\text{ns}$  typ.
- High Breakdown voltage :  $V_{CBO}=1500\text{V}$ .
- High reliability (Adoption of HVP process).
- Adoption of MBIT process.
- On-chip damper diode.

### Package Dimensions

unit: mm

#### 2039C-TO3PML



### Specifications

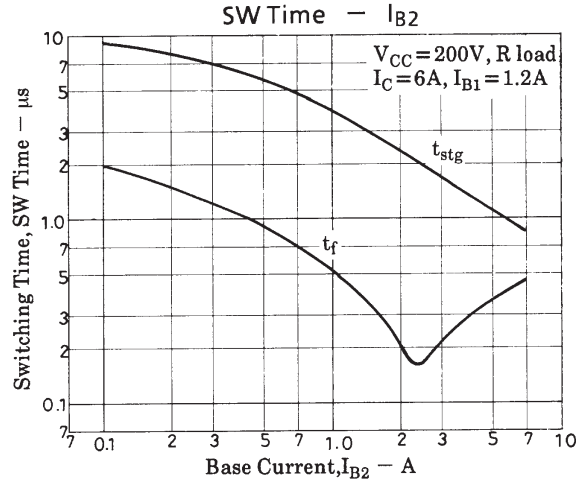
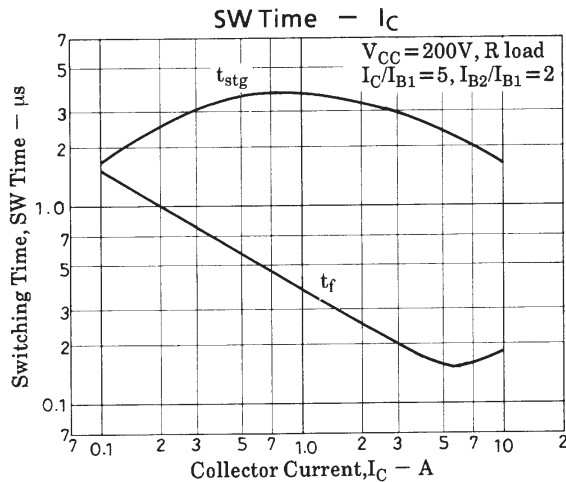
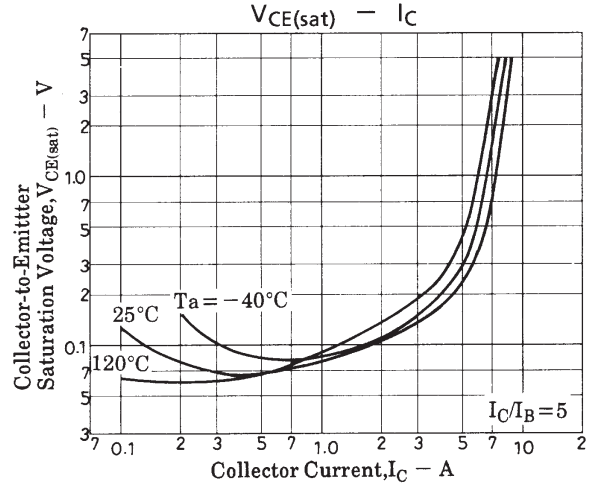
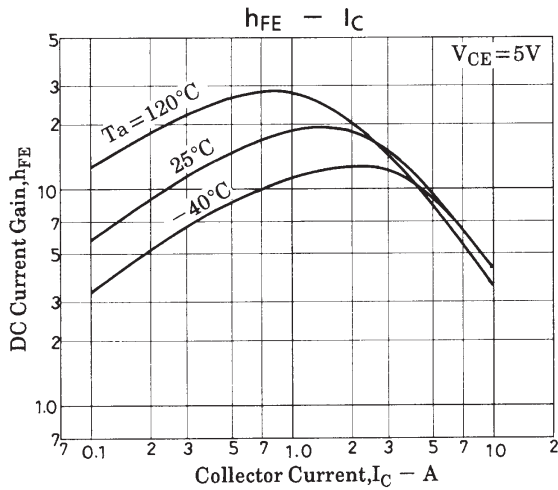
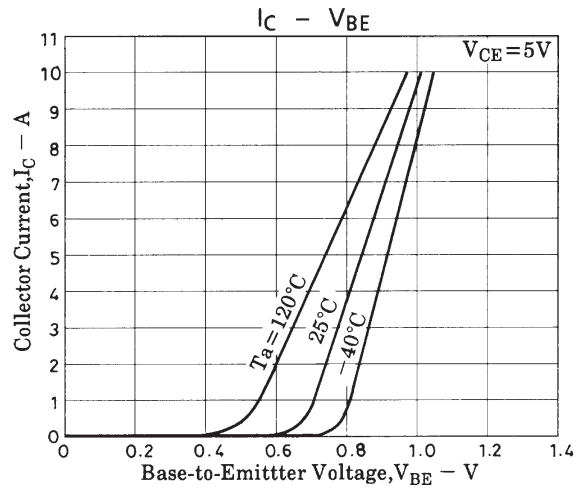
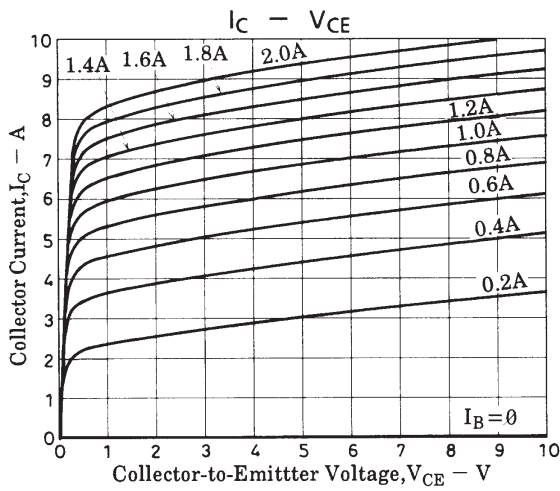
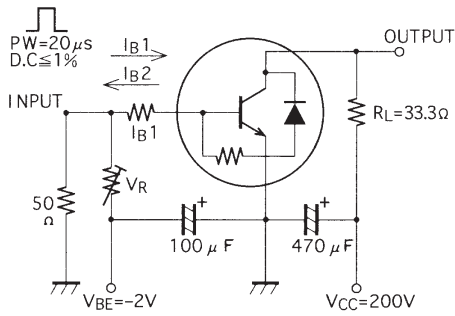
#### Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	$V_{CBO}$		1500	V
Collector-to-Emitter Voltage	$V_{CEO}$		800	V
Emitter-to-Base Voltage	$V_{EBO}$		6	V
Collector Current	$I_C$		10	A
Collector Current (Pulse)	$I_{CP}$		25	A
Collector Dissipation	$P_C$		3.0	W
		$T_c=25^\circ\text{C}$	70	W
Junction Temperature	$T_j$		150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$		-55 to +150	$^\circ\text{C}$

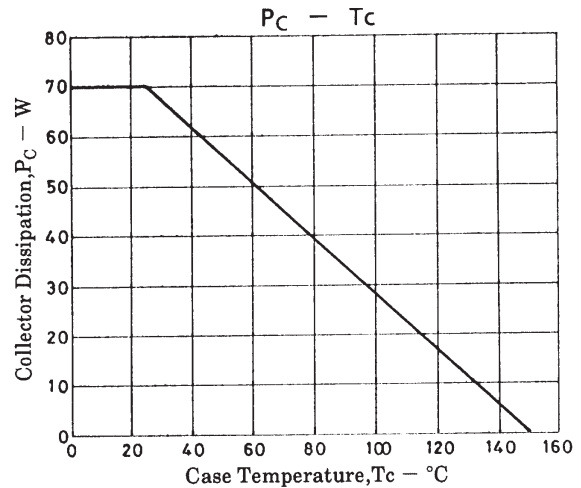
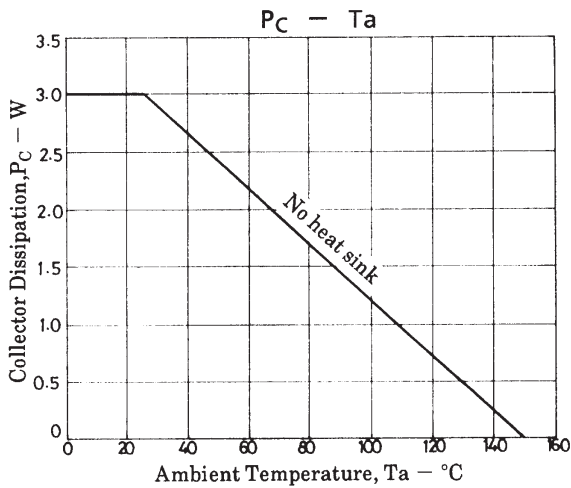
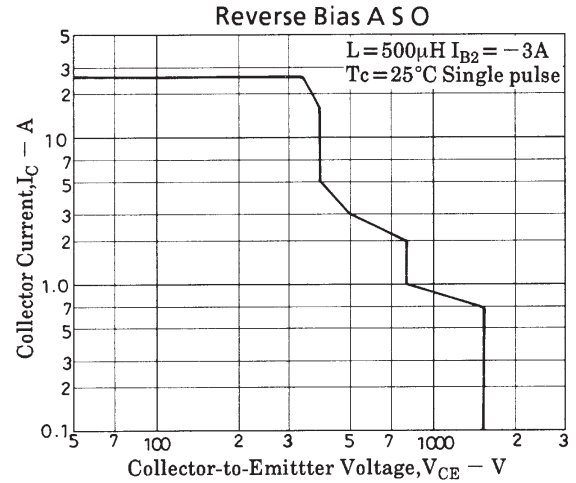
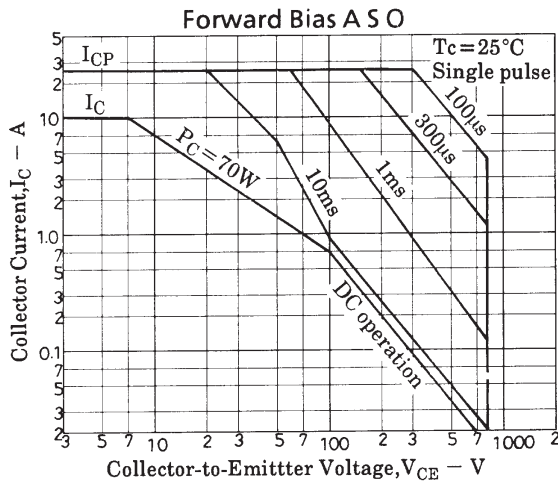
#### Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=800\text{V}, I_E=0$			10	$\mu\text{A}$
Collector Cutoff Current	$I_{CES}$	$V_{CE}=1500\text{V}, R_{BE}=0$			1.0	mA
Collector Sustain Voltage	$V_{CEO(SUS)}$	$I_C=100\text{mA}, I_B=0$	800			V
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=4\text{V}, I_C=0$	40		130	mA
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=8\text{A}, I_B=2\text{A}$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=8\text{A}, I_B=2\text{A}$			1.5	V
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5\text{V}, I_C=1\text{A}$	15		25	
	$h_{FE(2)}$	$V_{CE}=5\text{V}, I_C=8\text{A}$	4		7	
Storage Time	$t_{stg}$	$I_C=6\text{A}, I_{B1}=1.2\text{A}, I_{B2}=-2.4\text{A}$			3.0	$\mu\text{s}$
Fall Time	$t_f$	$I_C=6\text{A}, I_{B1}=1.2\text{A}, I_{B2}=-2.4\text{A}$		0.1	0.2	$\mu\text{s}$

Switching Time Test Circuit



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